

CRYSTAL GROWTH METHOD

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Patent Number: JP1154511
Publication date: 1989-06-16
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Requested Patent: ☐ JP1154511
Application Number: JP19870311915 19871211
Priority Number(s):
IPC Classification: H01L21/20; H01S3/18
EC Classification:
EC Classification:
Equivalents: JP2828979B2

Abstract

PURPOSE: To enable forming a heterojunction between materials having different crystal structures, by using the so-called atomic layer epitaxial growth method wherein a crystal is grown one atomic layer by one atomic layer, by supplying anion and cation alternately in time domain, to the boundary surface of solid phase crystal growth.

CONSTITUTION: The face (100) of zinc blended structure crystal is alternately laminated with monoatomic layers of anion and cation. In the case where the surface of the face (100) is formed by anion, when cation of a material, which originally has wurtzite structure, reaches the surface, bond to take wurtzite structure does not come out, so that it is taken in a lattice position of cation of the wurtzite structure. In this manner, by supplying anion and cation alternately in time domain to the growth boundary surface, the one which is originally wurtzite structure is turned into zinc blende structure being crystal structure of substrate, and excellent heterojunction is obtained.